

Amendments to the Claims:

This listing of the claims will replace all prior versions and listings of claims in the application:

Listing of the Claims:

1 – 9. (Canceled)

10. (Original) A semiconductor device comprising:

a first hydrogen barrier film having an oxidized region in a surface thereof;

a capacitor device formed on the first hydrogen barrier film; and

a second hydrogen barrier film which contains oxygen and which is formed to cover the capacitor device,

wherein the first and second hydrogen barrier films adhere to each other by oxygen bonding while the oxidized region located around the perimeter of the capacitor device is interposed therebetween.

11. (Original) A semiconductor device comprising:

a first hydrogen barrier film having a nitrated region in a surface thereof;

a capacitor device formed on the first hydrogen barrier film; and

a second hydrogen barrier film which contains nitrogen and which is formed to cover the capacitor device,

wherein the first and second hydrogen barrier films adhere to each other by nitrogen bonding while the nitrated region located around the perimeter of the capacitor device is interposed therebetween.

12. (Previously Presented) The semiconductor device of claim 10 or 11, wherein the first and second hydrogen barrier films adhere to each other so that no silicon oxide film is interposed between the first and second hydrogen barrier films.

13. (Previously Presented) The semiconductor device of claim 10 or 11, wherein the first and second hydrogen barrier films are films made of the same material.

14. (Previously Presented) The semiconductor device of claim 10 or 11, wherein the capacitor device comprises a lower electrode formed above the first hydrogen barrier film, a capacitor insulating film formed on the lower electrode, and an upper electrode formed on the capacitor insulating film, and

the capacitor insulating film is made of a ferroelectric film or a high dielectric film.

15. (Currently Amended) The semiconductor device of claim 14, wherein the capacitor insulating film is made of $[(\text{SrBi}_2(\text{Ta}_x\text{Nb}_{1-x})_2\text{O}_9)]$ $\text{SrBi}_2(\text{Ta}_x\text{Nb}_{1-x})_2\text{O}_9$, $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$, $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$, $[(\text{Bi}_x\text{La}_{1-x})_4\text{Ti}_3\text{O}_{12}]$ $(\text{Bi}_x\text{La}_{1-x})_4\text{Ti}_3\text{O}_{12}$ (where x satisfies $0 \leq x \leq 1$ in the above chemical formulas), or Ta_2O_5 .

16 - 38. (Canceled)